SKiiP 14NAB066V1



MiniSKiiP[®]1

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKiiP 14NAB066V1

Features

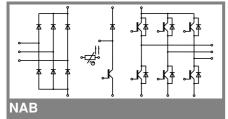
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 6,3 kVA
- Typical motor power 4,0 kW

Remarks

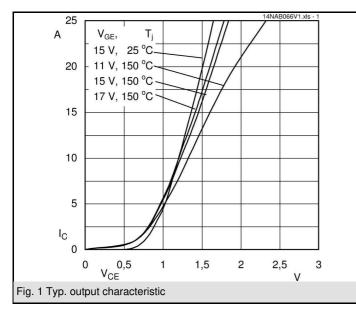
- Case temperature limited to T_C= 125°C max.
- Product reliability results are valid for T_i = 150°C
- SC data: $t_p \le 6$ s; $V_{GE} \le 15$ V; T_j = 150°C; V_{CC} = 360 V
- V_{CEsat}, V_F= chip level value

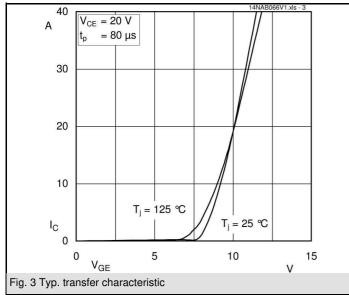


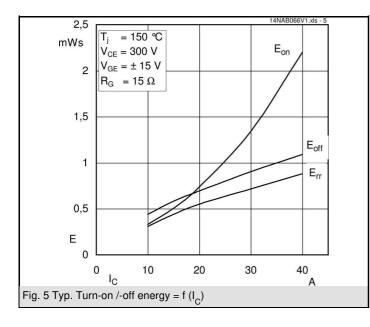
Absolute	Maximum Ratings	T_S = 25 °C, unless otherwise specified					
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V _{CES}		600	V				
I _C	T _s = 25 (70) °C, T _j = 150 °C	30 (21)	А				
I _C	T _s = 25 (70) °C, T _j = 175 °C	33 (25)	А				
I _{CRM}	$t_p = 1 \text{ ms}$	40	А				
V _{GES}		±20	V				
Diode - Inverter, Chopper							
I _F	T _s = 25 (70) °C, T _i = 150 °C	24 (16)	А				
I _F	T _s = 25 (70) °C, T _j = 175 °C	31 (23)	А				
I _{FRM}	t _p = 1 ms	40	А				
Diode - Rectifier							
V _{RRM}		800	V				
I _F	T _s = 70 °C	35	А				
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	220	А				
i²t	t _p = 10 ms, sin 180 °, T _j = 25 °C	240	A²s				
I _{tRMS}	per power terminal (20 A / spring)	20	А				
T _i	IGBT, Diode	-40+175	°C				
T _{stg}		-40+125	°C				
V _{isol}	AC, 1 min.	2500	V				

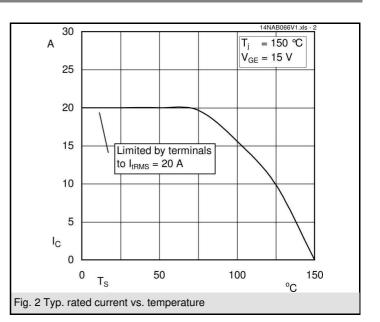
Characteristics			$T_S = 25 \text{ °C}$, unless otherwise specified					
Symbol	Conditions	1	min.	typ.	max.	Units		
IGBT - Inverter, Chopper								
V _{CE(sat)}	I _{Cnom} = 20 A, T _i = 25 (150) °C		1,1	1,45 (1,65)	1,85 (2,05)	V		
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$			5,8		V		
V _{CE(TO)}	T _j = 25 (150) °C			0,9 (0,85)	1 (0,9)	V		
r _{CE}	T _j = 25 (150) °C			30 (42,5)	45 (60)	mΩ		
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz			1,13		nF		
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz			0,25		nF		
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz			0,18		nF		
R _{CC'+EE'}	spring contact-chip T _s = 25 (150)°C					mΩ		
R _{th(j-s)}	per IGBT			1,6		K/W		
t _{d(on)}	under following conditions			20		ns		
t _r	$V_{CC} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$			30		ns		
t _{d(off)}	I _{Cnom} = 20 A, T _j = 150 °C			170		ns		
t _f	$R_{Gon} = R_{Goff} = 15 \Omega$			55		ns		
E_{on} (E_{off})	inductive load			0,75 (0,7)		mJ		
Diode - In	verter, Chopper							
$V_{F} = V_{EC}$	I _F = 20 A, T _i = 25 (150) °C			1,6 (1,65)	1,9 (1,95)	V		
V _(TO)	T _i = 25 (150) °C			1 (0,9)	1,1 (1)	V		
r _T	T _i = 25 (150) °C			30 (37,5)	40 (47,5)	mΩ		
R _{th(j-s)}	per diode			2,5		K/W		
I _{RRM}	under following conditions			27		А		
Q _{rr}	I _{Enom} = 20 A, V _R = 300 V			2,25		С		
E _{rr}	$V_{GE} = 0 V, T_i = 150^{\circ}C$			0,55		mJ		
	di _F /dt = 1280 A/ s							
Diode- Re	ectifier							
V _F	I _{Fnom} = 15 A, T _i = 25 °C			1,1		V		
V _(TO)	$T_{i} = 150 \ ^{\circ}C$			0,8		V		
r _T	T _i = 150 °C			20		mΩ		
R _{th(j-s)}	per diode			1,5		K/W		
Temperature Sensor								
R _{ts}	3 %, T _r = 25 (100) °C			1000(1670)		Ω		
Mechanical Data								
W				35		g		
M _s	Mounting torque		2		2,5	Nm		

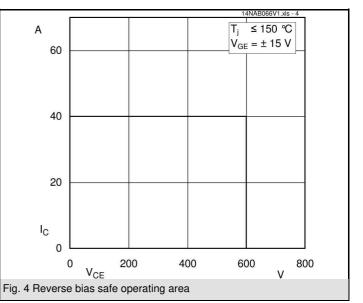
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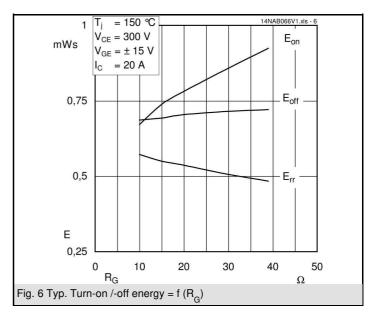




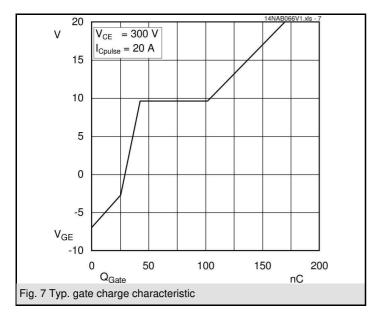


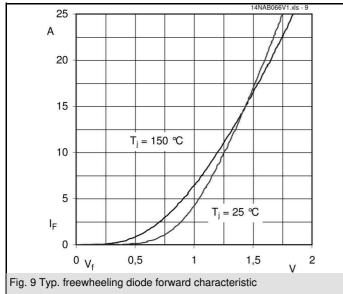


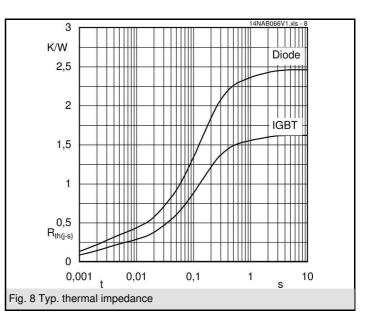


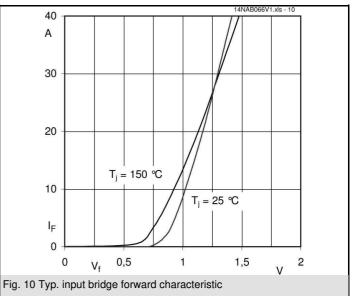


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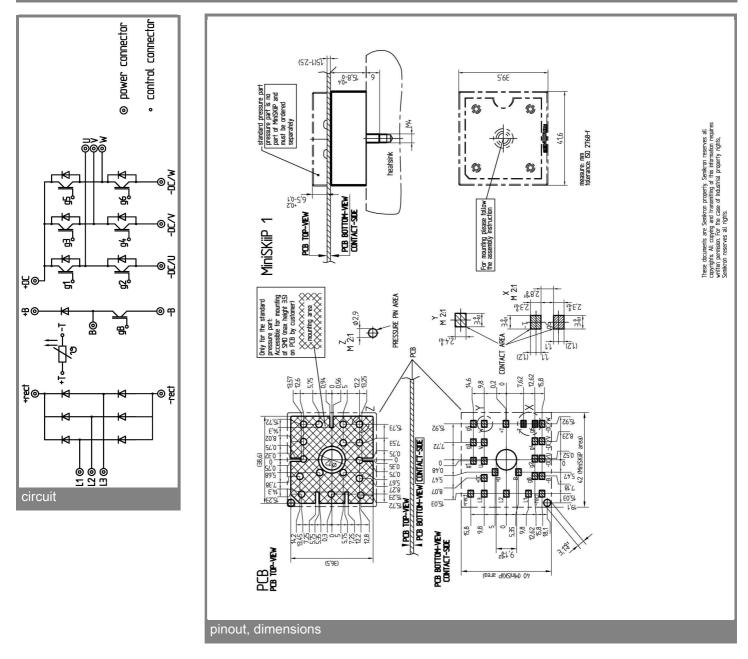








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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.